

Technical Data
Data Sheet N1238. Rev. -

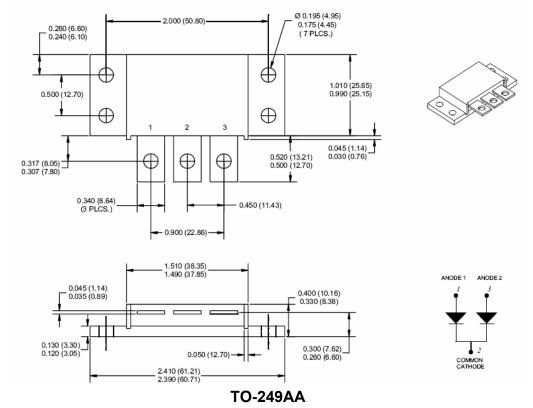
Green Products

166CMQ200 SCHOTTKY RECTIFIER

Applications:

- Switching power supply Converters Free-Wheeling diodes Reverse battery protection Features:
 - 175 °C T_J operation
 - Isolated heatsink
 - · Low profile, high current package
 - Center tap module
 - Low forward voltage drop
 - High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
 - High frequency operation
 - Guard ring for enhanced ruggedness and long term reliability
 - This is a Pb Free Device
 - All SMC parts are traceable to the wafer lot
 - Additional testing can be offered upon request

Mechanical Dimensions: In Inches/mm



MARKING, MOLDING RESIN

Marking for 166CMQ200, 1st row SS YYWWL, 2nd row 166CMQ200, 3rd row 1 2 3 (Pin) Where YY is the manufacture year WW is the manufacture week code L is the wafer's Lot Number

Molding resin

Epoxy resin UL: 94V-0

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Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	VRWM	-	200	V
Max. Average Forward Current *	I _{F(AV)}	50% duty cycle @T _C =87°C, rectangular wave form	160	А
Max. Peak One Cycle Non- Repetitive Surge Current (peg leg)	I _{FSM}	8.3 ms, half Sine pulse	960	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V_{F1}	@ 80A, Pulse, T _J = 25 °C	1.10	V
	V_{F2}	@ 80A, Pulse, T _J = 75 °C	0.90	V
Max. Reverse Current (per leg) *	I _{R1}	$@V_R = \text{rated } V_R$ $T_J = 25 ^{\circ}\text{C}$	1.5	mA
	I _{R2}	$@V_R = \text{rated } V_R$ $T_J = 125 ^{\circ}C$	21	mA
Max. Junction Capacitance (per leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	900	pF
Typical Series Inductance (per leg)	L _S	Measured lead to lead 5 mm from package body	5.0	nΗ
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

^{*} Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +175	°C
Max. Storage Temperature	T _{stg}	-	-55 to +175	°C
Maximum Thermal Resistance Junction to Case (per leg)	$R_{ heta JC}$	DC operation	1.0	°C/W
Maximum Thermal Resistance Junction to Case (per package)	$R_{ heta JC}$	DC operation	0.5	°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{\theta cs}$	Mounting surface, smooth and greased	0.10	°C/W
Mounting Torque	Тм	-	40(min)	Kg-cm
			58(max)	
Approximate Weight	wt	-	58	g
Case Style	TO-249AA			

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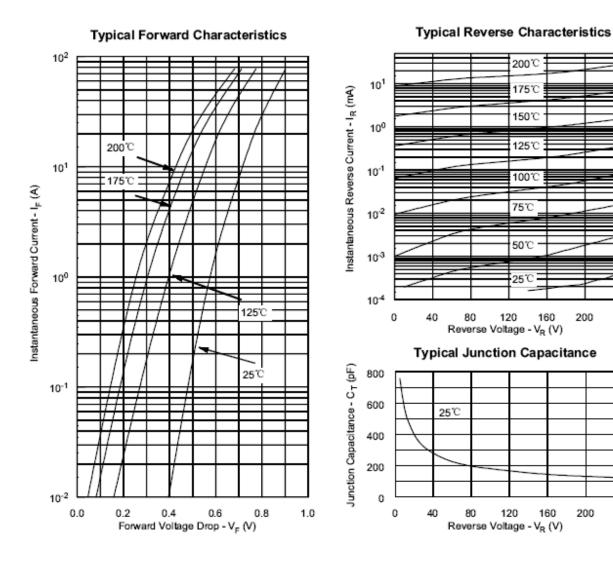
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